



ADVANCE INFORMATION

# HAL114

## Hall Effect Sensor IC

Edition May 5, 1997  
6251-456-1AI

 **MICRONAS**  

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**INTERMETALL**

## Hall Effect Sensor IC in CMOS technology

### Features:

- operates from 4.5 V to 24 V supply voltage
- overvoltage and reverse-voltage protection
- short-circuit protected open-drain output switch
- operates with magnetic fields from DC to 20 kHz
- on-chip temperature compensation circuitry minimizes shifts in on and off points and hysteresis over temperature and supply voltage
- the decrease of magnetic flux density caused by rising temperature in the sensor system is compensated by a built-in negative temperature coefficient of hysteresis
- ideal sensor for ignition timing, anti-block brake systems and speed measurement in hostile automotive and industrial environments
- EMC corresponding to DIN 40839

### Specifications

- switching type: unipolar
- output low with magnetic southpole on branded side of package
- output turns high if magnetic field is removed

### Marking Code

Type	Temperature Range		
	A	E	C
HAL 114S HAL 114UA	114A	114E	114C

### Operating Junction Temperature Range

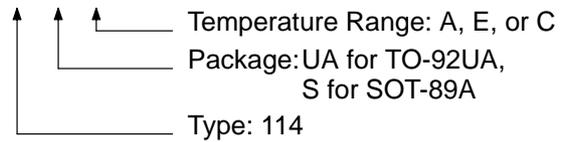
**A:**  $T_J = -40\text{ °C to }+170\text{ °C}$

**E:**  $T_J = -40\text{ °C to }+100\text{ °C}$

**C:**  $T_J = 0\text{ °C to }+100\text{ °C}$

### Designation of Hall Sensors

HALXXXPP-T

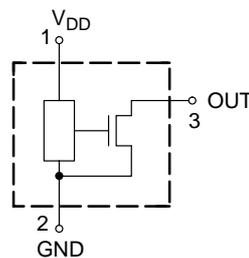


Example: **HAL 114UA-E**

- Type: 114
- Package: TO-92UA
- Temperature Range:  $T_J = -40\text{ °C to }+100\text{ °C}$

### Solderability

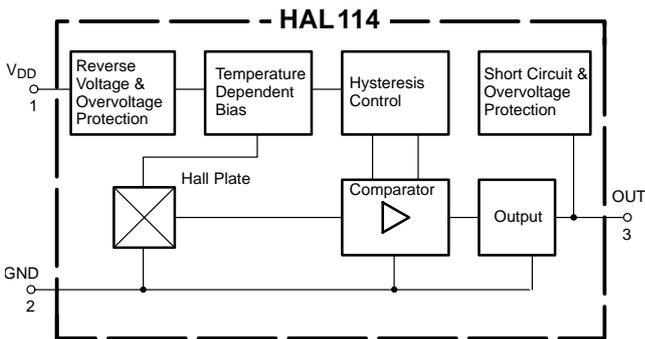
- Package SOT-89A: according to IEC68-2-58
- Package TO-92UA: according to IEC68-2-20



**Fig. 1:** Pin configuration

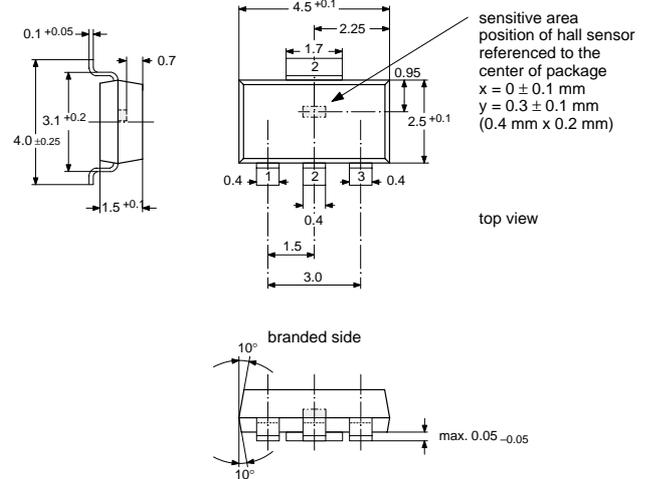
**Functional Description**

This Hall effect sensor is a monolithic integrated circuit that switches in response to magnetic fields. If a magnetic field with flux lines at right angles to the sensitive area is applied to the sensor, the biased Hall plate forces a Hall voltage proportional to this field. The Hall voltage is compared with the actual threshold level in the comparator. The temperature-dependent bias increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the magnetic field exceeds the threshold levels, the open drain output switches to the appropriate state. The built-in hysteresis eliminates oscillation and provides switching behavior of output without bounce. The output is short-circuit protected by limiting high currents and by sensing excess temperature. Shunt protection devices clamp voltage peaks at the Output-Pin and VDD-Pin together with external series resistors. Reverse current is limited at the V<sub>DD</sub>-Pin by an internal series resistor up to -15 V. No external reverse protection diode is needed at the V<sub>DD</sub>-Pin for values ranging from 0 V to -15 V.

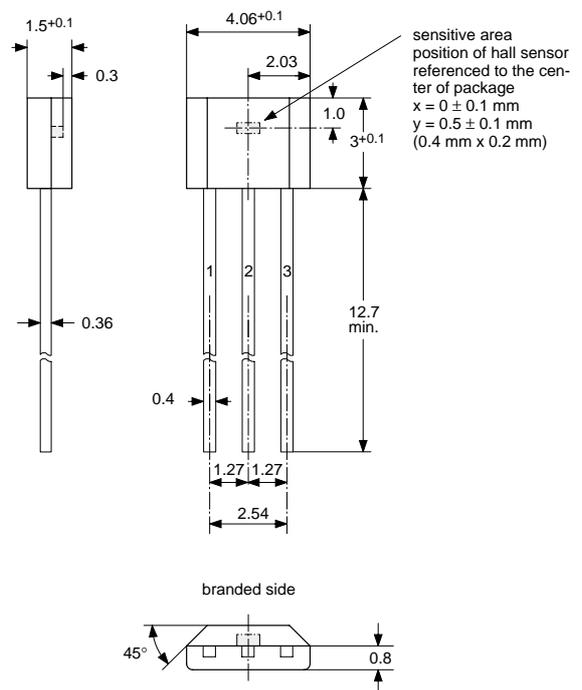


**Fig. 2:** HAL 114 block diagram

**Outline Dimensions**



**Fig. 3:** Plastic Small Outline Transistor Package (SOT-89A)  
Weight approximately 0.04 g  
Dimensions in mm



**Fig. 4:** Plastic Transistor Single Outline Package (TO-92UA)  
Weight approximately 0.12 g  
Dimensions in mm

**Absolute Maximum Ratings**

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V <sub>DD</sub>	Supply Voltage	1	-15	28 <sup>1)</sup>	V
-V <sub>P</sub>	Test Voltage for Supply	1	-24 <sup>2)</sup>	-	V
-I <sub>DD</sub>	Reverse Supply Current	1	-	50 <sup>1)</sup>	mA
I <sub>DDZ</sub>	Supply Current through Protection Device	1	-300 <sup>3)</sup>	300 <sup>3)</sup>	mA
V <sub>OH</sub>	Output High Voltage	3	-	28 <sup>1)</sup>	V
I <sub>O</sub>	Continuous Output On Current	3	-	30	mA
I <sub>Omax</sub>	Peak Output On Current	3	-	250	mA
I <sub>OZ</sub>	Output Current through Protection Device	3	-300 <sup>3)</sup>	300 <sup>3)</sup>	mA
T <sub>S</sub>	Storage Temperature Range		-65	150	°C
T <sub>J</sub>	Junction Temperature Range		-40 -40	150 170 <sup>4)</sup>	°C

<sup>1)</sup> as long as T<sub>Jmax</sub> is not exceeded  
<sup>2)</sup> with a 220 Ω series resistance at pin 1 corresponding to test circuit 1  
<sup>3)</sup> t < 2 ms  
<sup>4)</sup> t < 1000h

Stresses beyond those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the “Recommended Operating Conditions/Characteristics” of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

**Recommended Operating Conditions**

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit
V <sub>DD</sub>	Supply Voltage	1	4.5	-	24	V
I <sub>O</sub>	Continuous Output On Current	3	0	-	20	mA
R <sub>S</sub>	Series Resistor	1	-	-	270	Ω

**Electrical Characteristics** at  $T_J = -40\text{ °C}$  to  $+170\text{ °C}$ ,  $V_{DD} = 4.5\text{ V}$  to  $24\text{ V}$ , as not otherwise specified  
 Typical Characteristics for  $T_J = 25\text{ °C}$  and  $V_{DD} = 12\text{ V}$

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Test Conditions
$V_{OL}$	Output Voltage	3	–	120	250	mV	$I_O = 12.5\text{ mA}$ , $T_J = 25\text{ °C}$
$V_{OL}$	Output Voltage over Temperature Range	3	–	120	400	mV	$I_O = 12.5\text{ mA}$
$V_{OL}$	Output Voltage over Temperature Range	3	–	190	500	mV	$I_{OL} = 20\text{ mA}$
$I_{OH}$	Output Leakage Current	3	–	–	1	$\mu\text{A}$	$B < B_{off}$ , $V_{OH} = 24\text{ V}$ , $T_J = 25\text{ °C}$
$I_{OH}$	Output Leakage Current over Temperature Range	3	–	–	10	$\mu\text{A}$	$B < B_{off}$ $V_{OH} = 24\text{ V}$ , $T_J < 150\text{ °C}$
$I_{DD}$	Supply Current	1	6.6	8.3	11	mA	$T_J = 25\text{ °C}$
$I_{DD}$	Supply Current over Temperature Range	1	3.9	8.3	12	mA	
$t_{en(O)}$	Enable Time of Output after Setting of $V_{DD}$	3	–	6	10	$\mu\text{s}$	$V_{DD} = 12\text{ V}$
$t_r$	Output Rise Time	3	–	85	400	ns	$V_{DD} = 12\text{ V}$ , $R_L = 820\text{ Ohm}$ , $CL = 20\text{ pF}$
$t_f$	Output Fall Time	3	–	60	400	ns	$V_{DD} = 12\text{ V}$ , $R_L = 820\text{ Ohm}$ , $CL = 20\text{ pF}$
$R_{thJSB}$ case SOT-89A	Thermal Resistance Junction to Substrate Backside		–	150	200	K/W	Fiberglass Substrate pad size see Fig. 6
$R_{thJA}$ case TO-92UA	Thermal Resistance Junction to Soldering Point		–	150	200	K/W	Leads at ambient temperature at a distance of 2 mm from case

**Magnetic Characteristics** at  $T_J = -40\text{ °C}$  to  $+170\text{ °C}$ ,  $V_{DD} = 4.5\text{ V}$  to  $24\text{ V}$ ,  
 Typical Characteristics for  $V_{DD} = 12\text{ V}$

Magnetic flux density values of switching points.

Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter	–40 °C			25 °C			100 °C			170 °C			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
On point $B_{ON}$	7.5	22.8	36.0	7.0	21.3	34.0	6.3	19.3	31.5	6.0	18.3	31.0	mT
Off point $B_{OFF}$	4.3	19.2	33.2	4.0	17.8	31.2	3.6	16.0	28.9	3.6	15.1	28.8	mT
Hysteresis $B_{HYS}$	2.8	3.6	4.3	2.8	3.5	4.2	2.6	3.3	4.0	2.2	3.2	3.9	mT

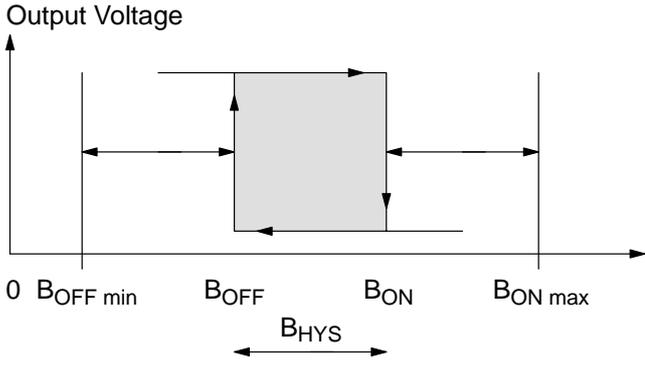


Fig. 5: Definition of switching points and hysteresis

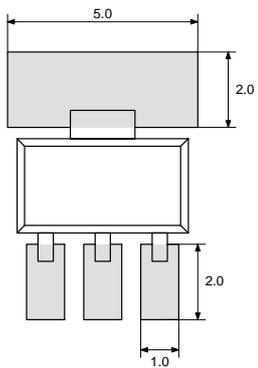
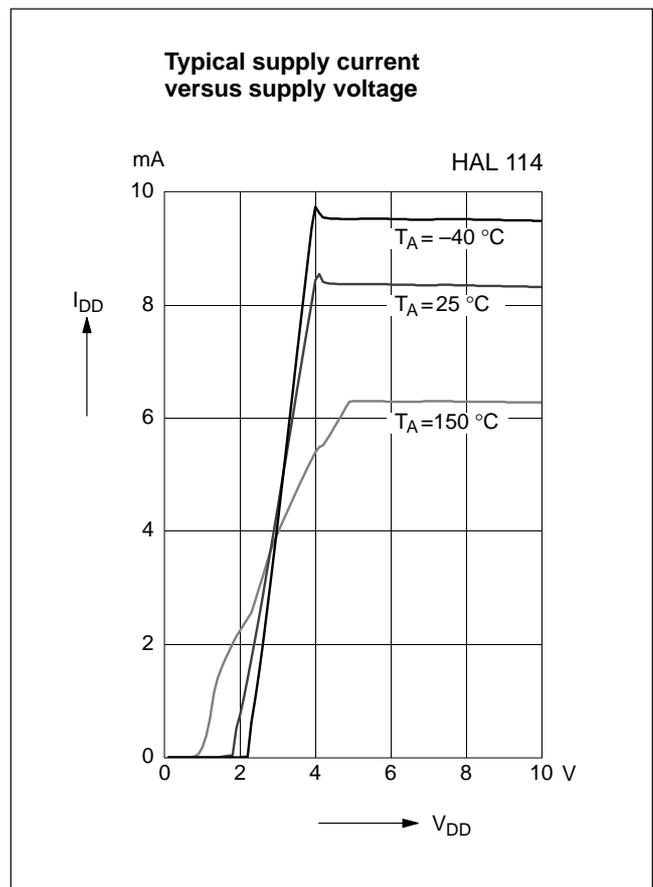
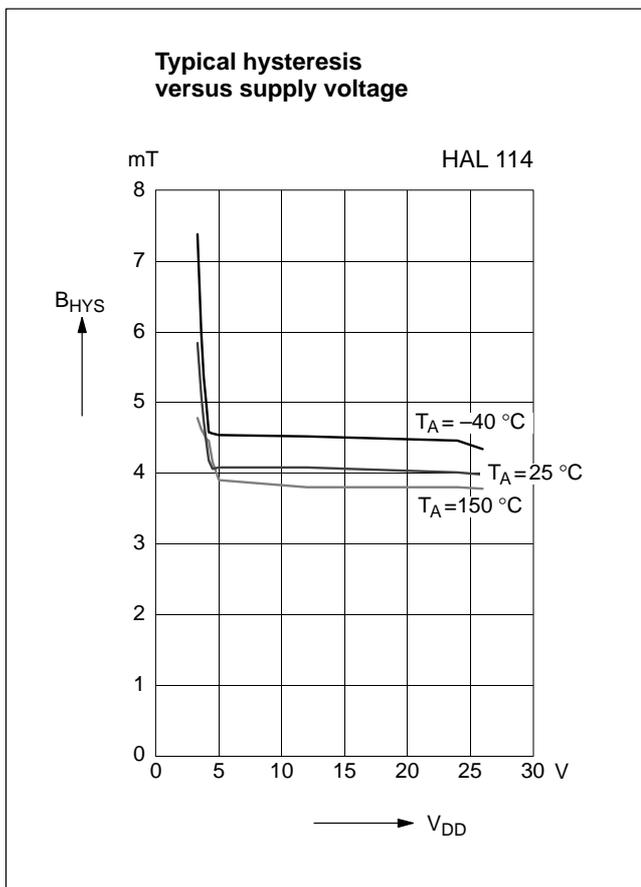
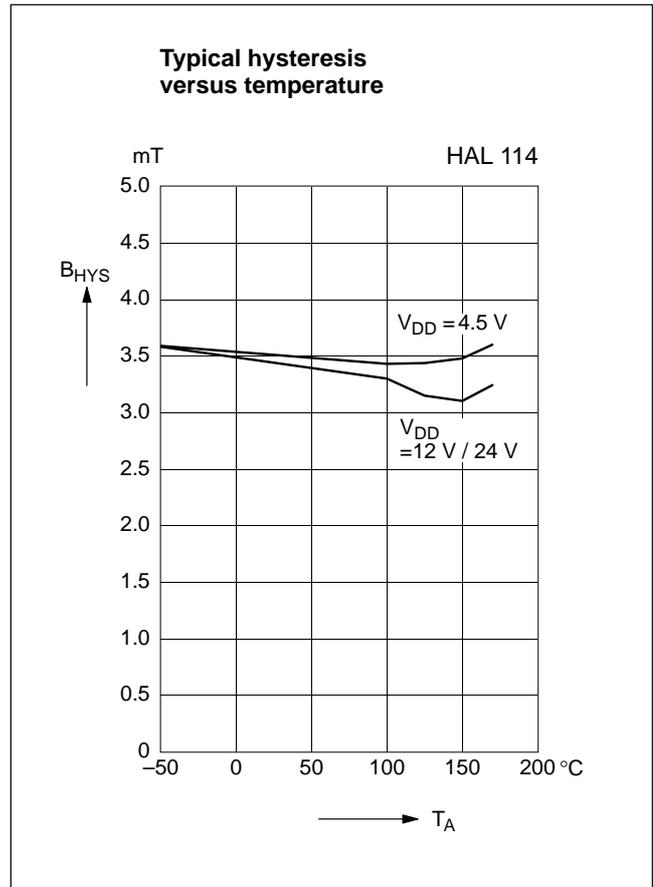
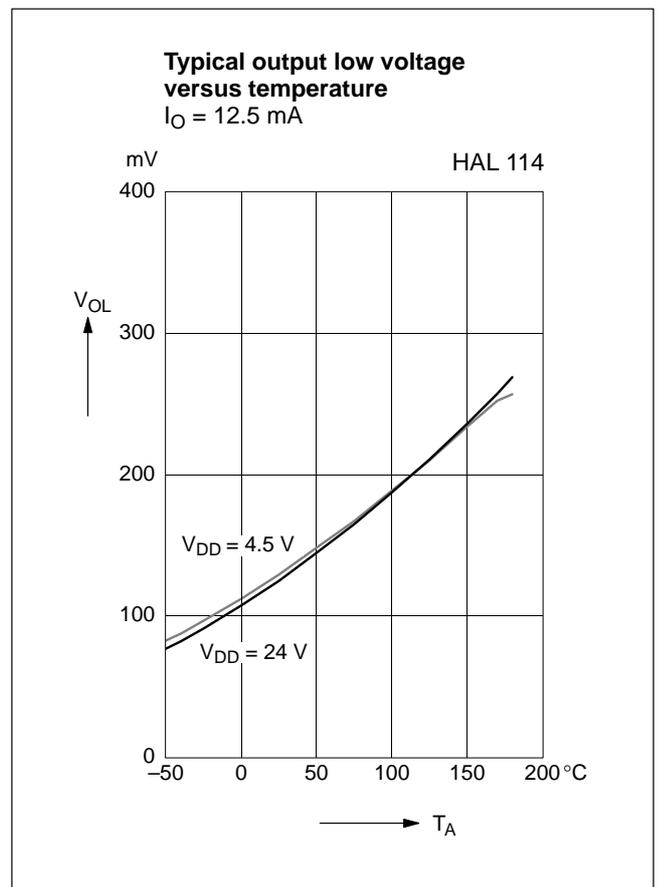
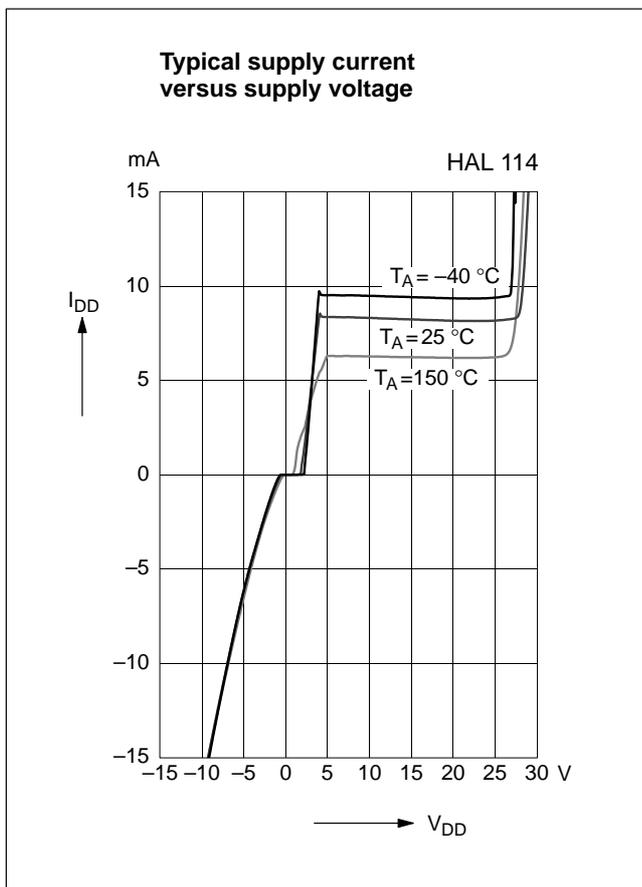
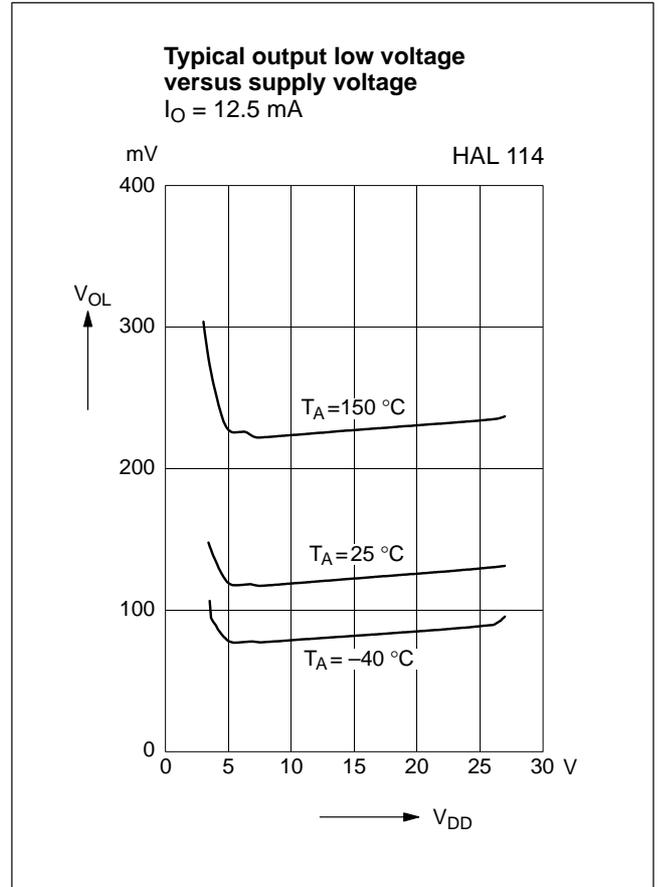
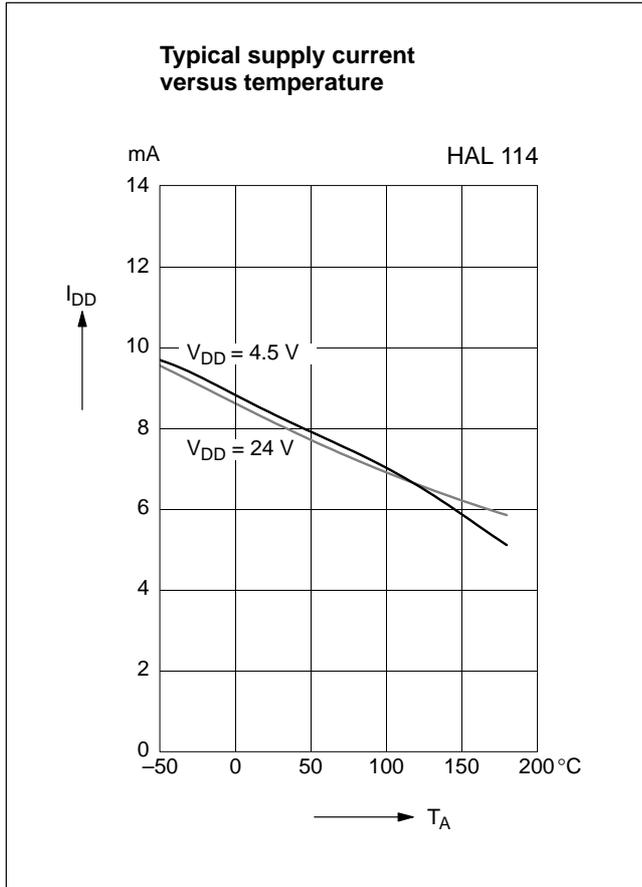
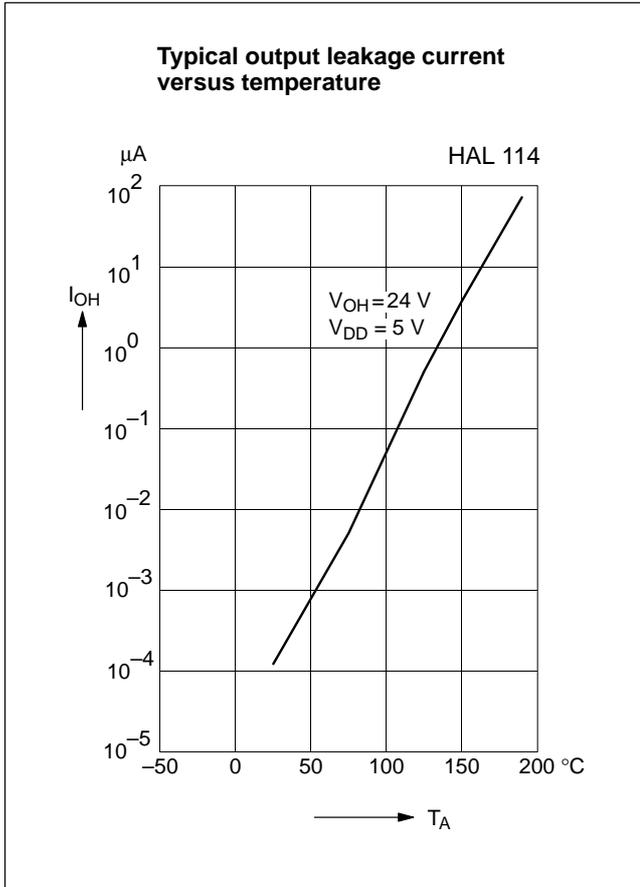


Fig. 6: Recommended pad size SOT-89A  
Dimensions in mm







**Application Note**

For electromagnetic immunity, it is recommended to apply a 330 pF minimum capacitor between  $V_{DD}$  (pin 1) and Ground (pin 2).

For applications requiring robustness to conducted disturbances (transients), a 220  $\Omega$  series resistor to pin 1 and a 4.7 nF capacitor between  $V_{DD}$  (pin1) and Ground (pin 2) is recommended.

The series resistor and the capacitor should be placed as close as possible to the IC.

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Printed in Germany  
 Order No. 6251-456-1A1

**Ambient Temperature**

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature  $T_J$ ) is higher than the temperature outside the package (ambient temperature  $T_A$ ).

$$T_J = T_A + \Delta T$$

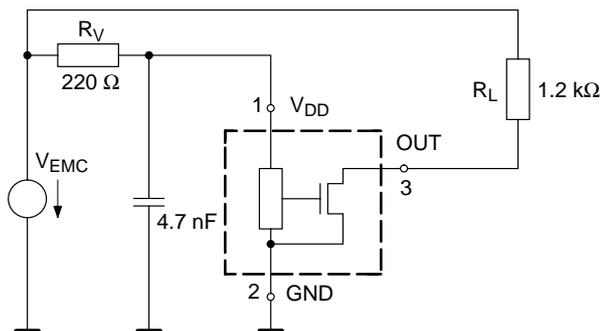
At static conditions, the following equations are valid:

- for SOT-89A:  $\Delta T = I_{DD} * V_{DD} * R_{thJSB}$
- for TO-92UA:  $\Delta T = I_{DD} * V_{DD} * R_{thJA}$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for  $I_{DD}$  and  $R_{th}$ , and the max. value for  $V_{DD}$  from the application.

**Test Circuits for Electromagnetic Compatibility**

Test pulses  $V_{EMC}$  corresponding to DIN 40839.



**Fig. 7:** Test circuit 1: test procedure for class C

**Data Sheet History**

1. Advance Information: "HAL 114 Hall Effect Sensor IC", May 5, 1997, 6251-456-1A1: First release of the advance information.

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